

Messrs. Rockwell Automation Co.,Ltd.

[查询"1MBH20D-060"供应商](#)

SPECIFICATION

Device Name IGBT

Type Name 1MBH20D-060-S06TT

Spec. No. MS5F-4086

Date June-11-1998

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Fuji Electric Co.,Ltd.
Matsumoto Factory

	DATE	NAME	APPROVED	Fuji Electric Co.,Ltd.	
DRAWN	June-11-98 K. Asada			DWG. NO.	MS5F4086
CHECKED	June-11-98 T. Igarashi				

H04-004-05

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This specification is applied to Fuji discrete IGBT 1MBH20D-060
supplied for Rockwell Automation Co., Ltd.

• Construction

1. Package dimension
There is a package dimension in 4/14 page .
2. Outview
There are no remarkable flaws on a product .
3. Indication
 - ① Trademark
 - ② Type Name
 - ③ Lot No.

• Ratings and Characteristics

1. There are some ratings and characteristics tables in 4/14 page and 5/14 page .
2. There are some performance curves in from 6/14 page to 14/14 page .

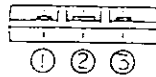
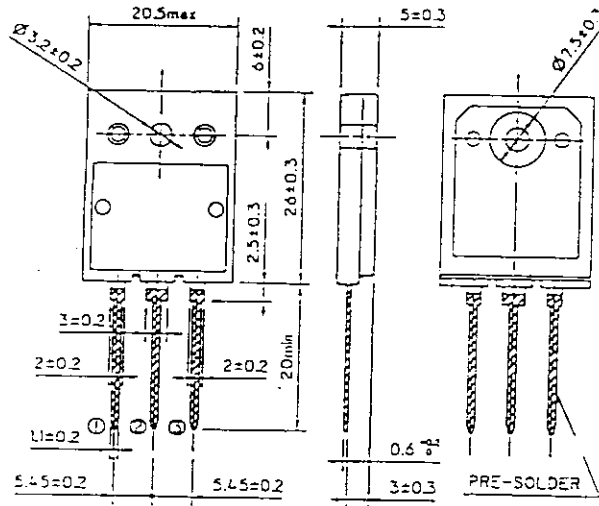
• Packing

Packing style follows our packing specification ~~MS500026~~.

MS5G CC3C (A)

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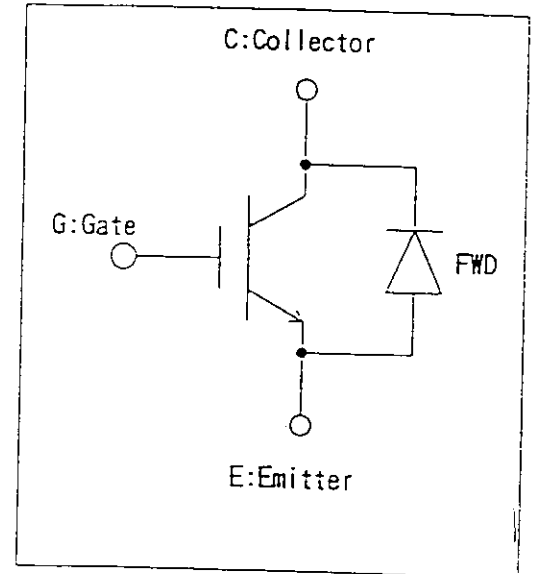
1. Outline Drawing



CONNECTION

- ① GATE
- ② COLLECTOR
- ③ EMITTER

2. Equivalent circuit



3. Absolute maximum ratings (Tc=25°C)

Items			Symbols	Ratings	Units
Collector-Emitter Voltage			V_{CES}	600	V
Gate-Emitter Voltage			V_{GES}	±22	V
Collector Current	DC	Tc=25 °C	I_{C25}	45	A
		Tc=110°C	I_{C110}	20	A
	1ms	Tc=25 °C	I_{cp}	152	A
IGBT Max. Power Dissipation			P_c	170	W
FWD Max. Power Dissipation			P_c	95	W
Operating Temperature			T_j	+ 150	°C
Storage Temperature			T_{stg}	-40 ~ +150	°C
Mounting Screw Torque			—	70	N · cm

4. Electrical Characteristics (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)

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Items		Symbols	Characteristics			Conditions	Unit
			min.	typ.	max.		
Zero gate voltage Collector Current		I_{CES}			1.0	$V_{GE} = 0V$ $V_{CE} = 600V$	mA
Gate-Emitter leakage Current		I_{GES}			20	$V_{CE} = 0V$ $V_{GE} = \pm 22V$	μA
Gate-Emitter Threshold Voltage		$V_{GE(th)}$	5.5		8.5	$V_{CE} = 20V$ $I_C = 20mA$	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			3.0	$V_{GE} = 15V$ $I_C = 20A$	V
Input capacitance		C_{ies}		1300		$V_{CE} = 0V$	pF
Output capacitance		C_{oes}		300		$V_{CE} = 10V$	
Reverse transfer capacitance		C_{res}		70		$f = 1MHz$	
Switching Time	Turn-on time	t_{on}			1.2	$V_{CC} = 300V$ $I_C = 20A$ $V_{GE} = \pm 15V$ $R_G = 120\Omega$ (Half Bridge)	μs
		t_r			0.6		
	Turn-off time	t_{off}			1.0		
		t_f			0.35		
	Turn-on time	t_{on}		0.16		$V_{CC} = 300V$ $I_C = 20A$ $V_{GE} = \pm 15V$ $R_G = 12\Omega$ (Half Bridge)	
		t_r		0.11			
	Turn-off time	t_{off}		0.30			
		t_f			0.35		
FWD forward voltage drop		V_F			3.0	$I_F = 20A$	V
Reverse recovery time		t_{rr}			0.3	$I_F=20A, V_{GE}=-10V$ $V_R= 200V$ $di/dt=100A/\mu s$	μs

5. Thermal resistance characteristics

Items	Symbols	Characteristics			Conditions	Unit
		min.	typ.	max.		
Thermal resistance	$R_{th(j-c)}$			0.73	IGBT	$^{\circ}\text{C}/\text{W}$
	$R_{th(j-c)}$			1.31	FWD	

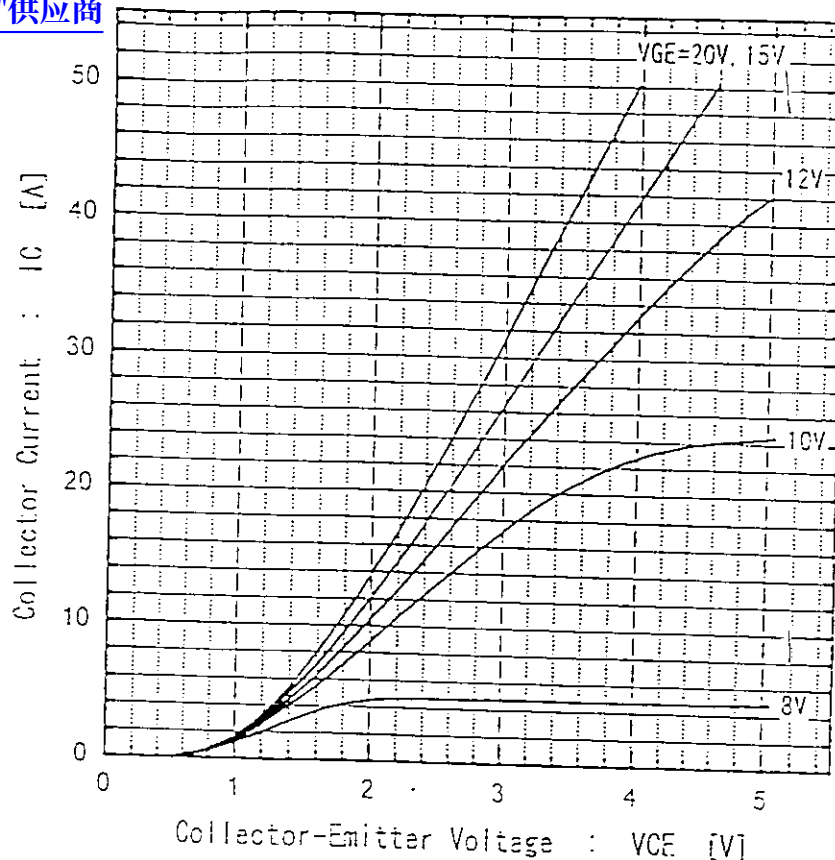
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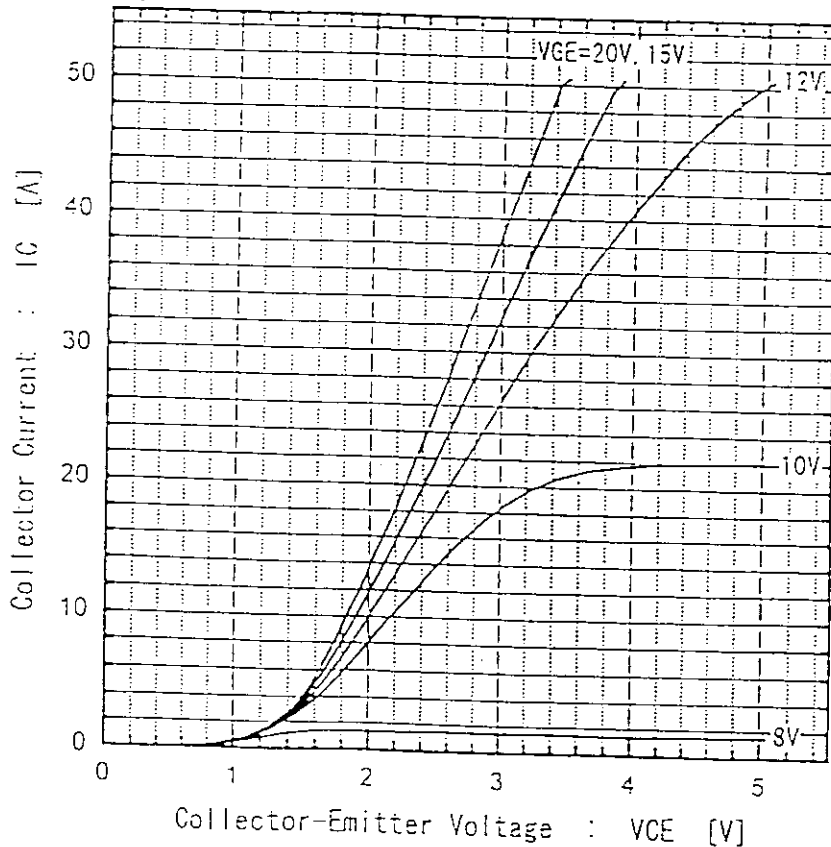
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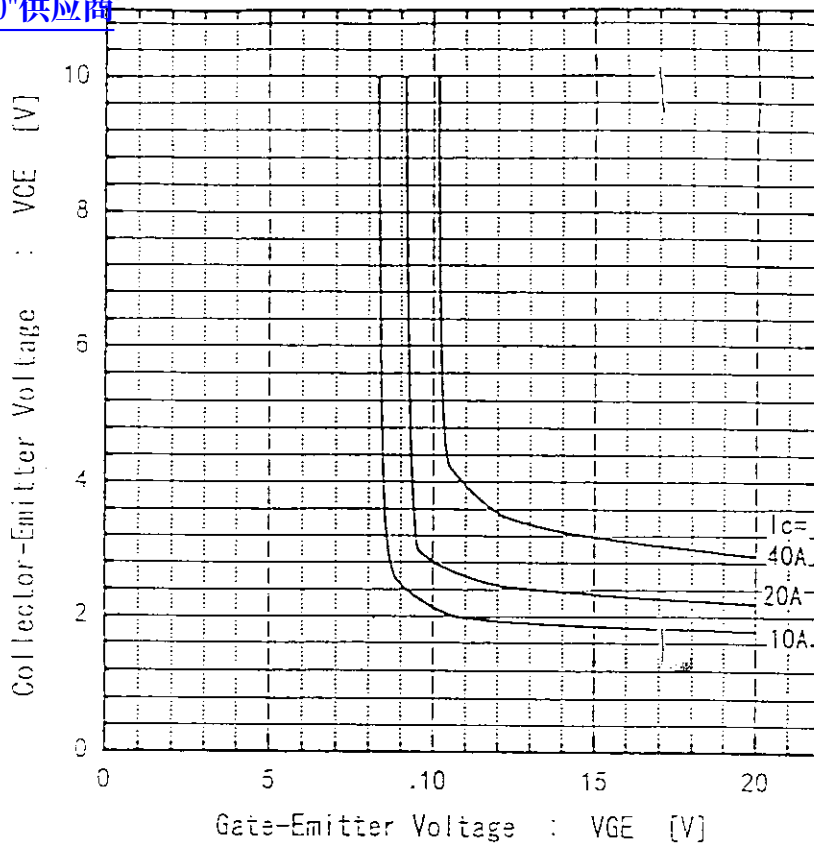
Collector Current vs. Collector-Emitter Voltage
T_j=125°C



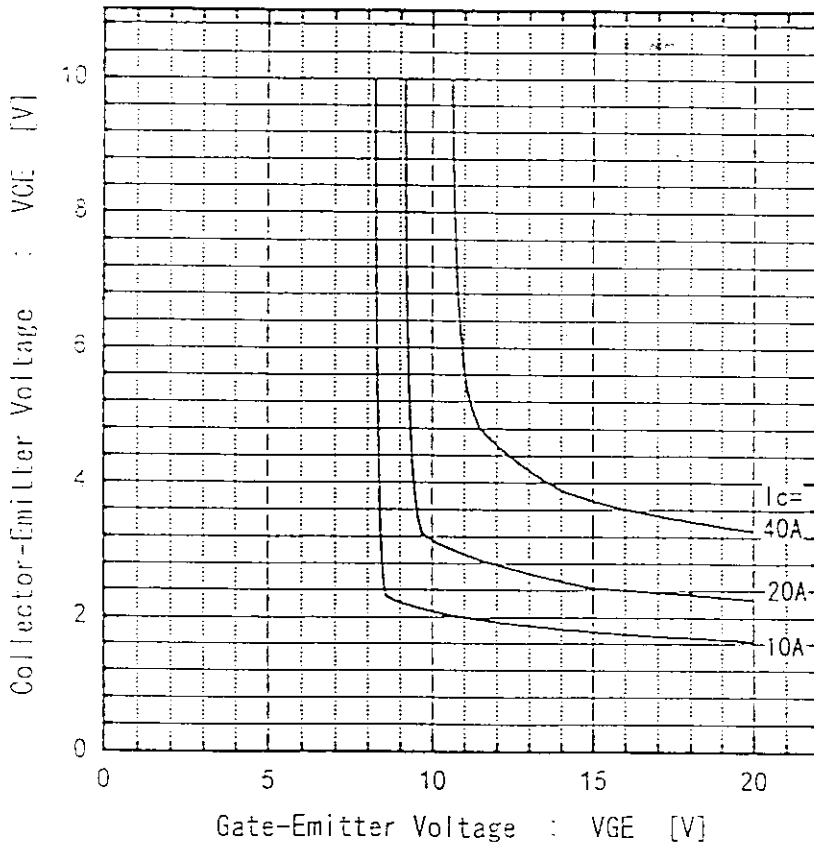
Collector Current vs. Collector-Emitter Voltage
T_j=25°C



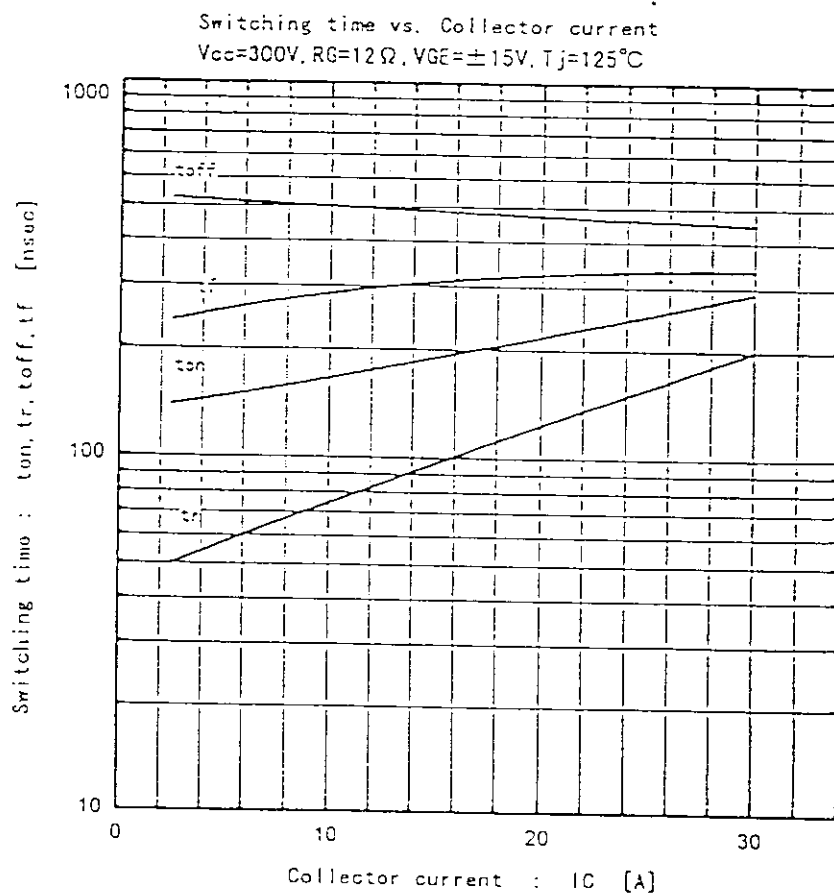
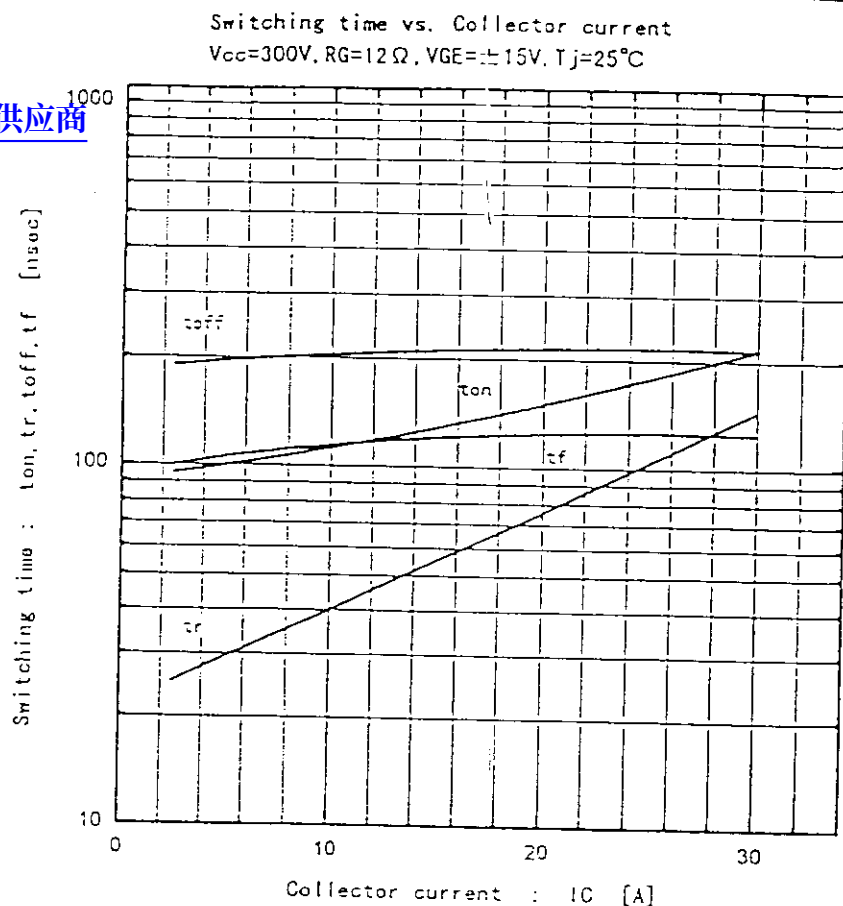
Collector-Emitter Voltage vs Gate-Emitter Voltage
Tj=25°C



Collector-Emitter Voltage vs Gate-Emitter Voltage
Tj=125°C

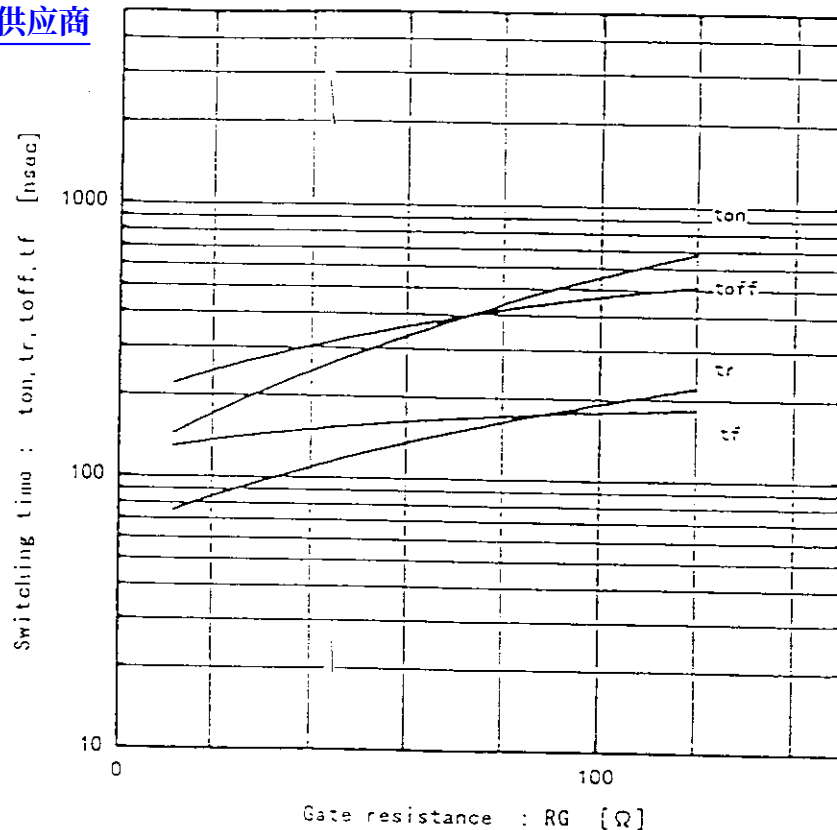


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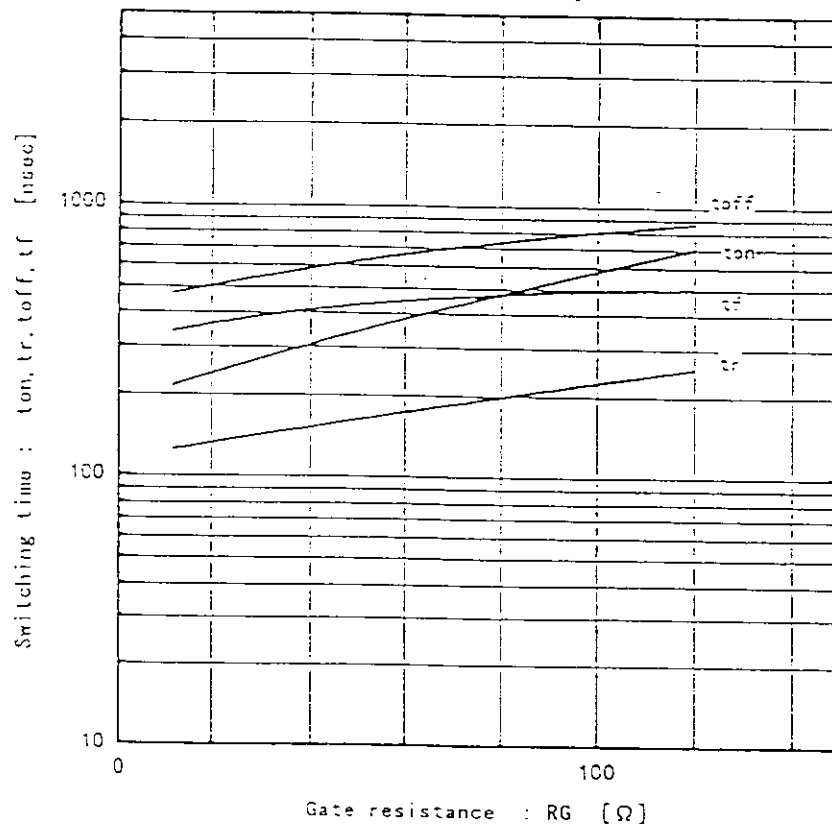


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Switching time vs. R_G
 $V_{CE}=300V$, $I_C=20A$, $V_{GE}=\pm 15V$, $T_J=25^\circ C$



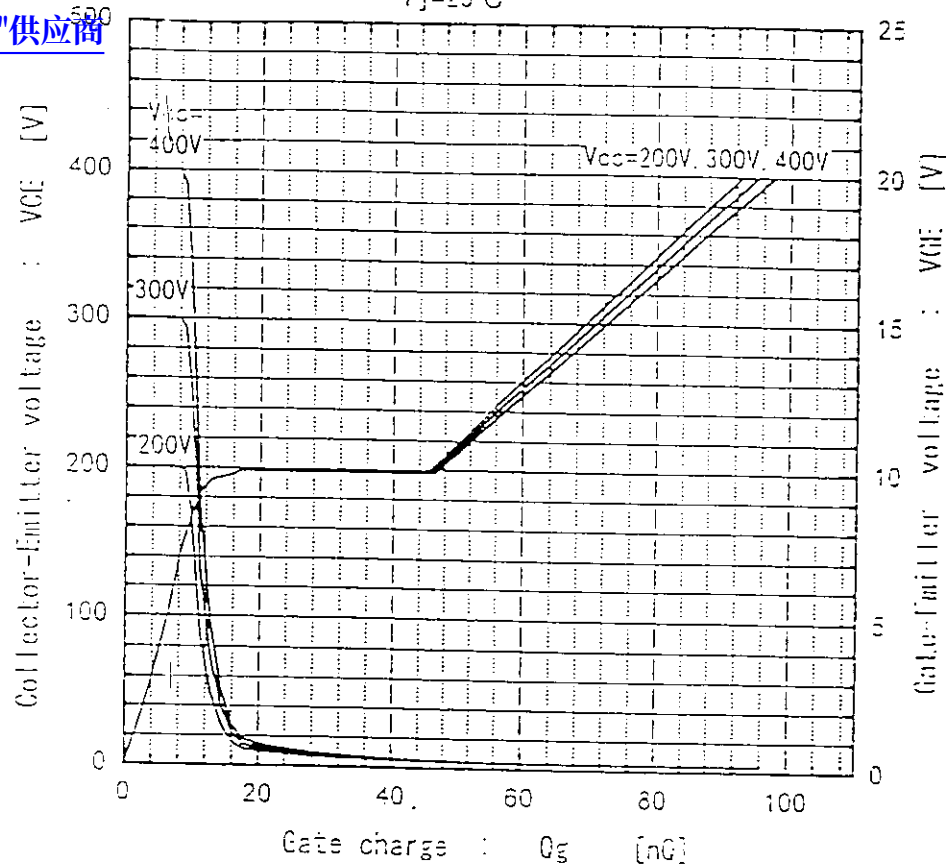
Switching time vs. R_G
 $V_{CE}=300V$, $I_C=20A$, $V_{GE}=\pm 15V$, $T_J=125^\circ C$



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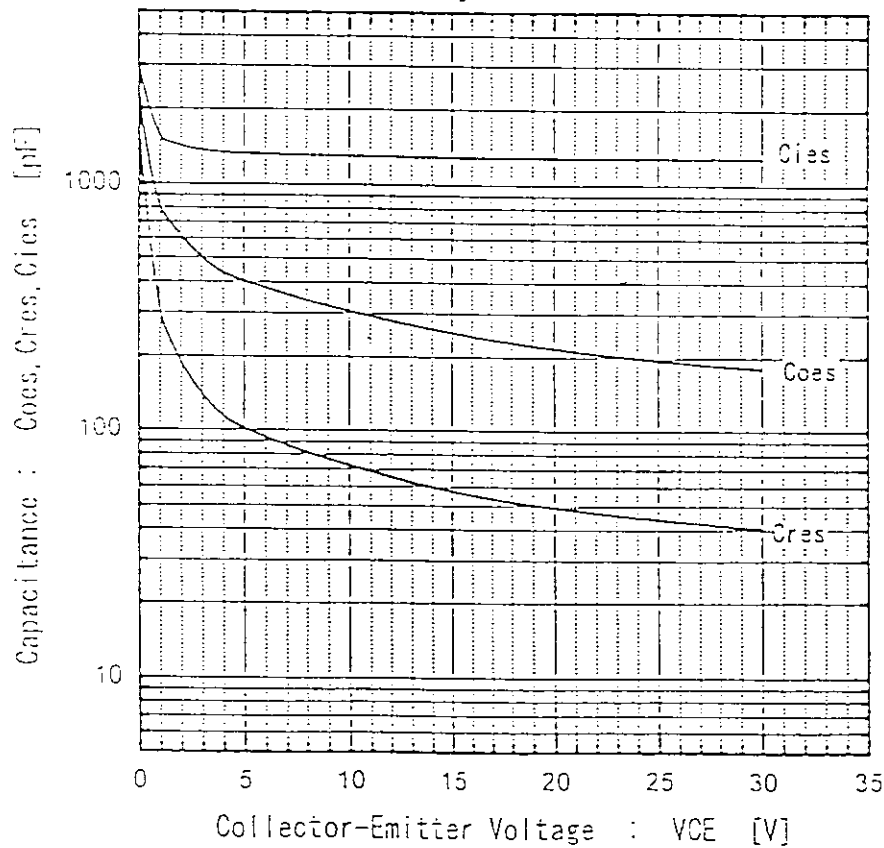
Dynamic input characteristics

$T_j=25^{\circ}\text{C}$



Capacitance vs. Collector-Emitter voltage

$T_j=25^{\circ}\text{C}$



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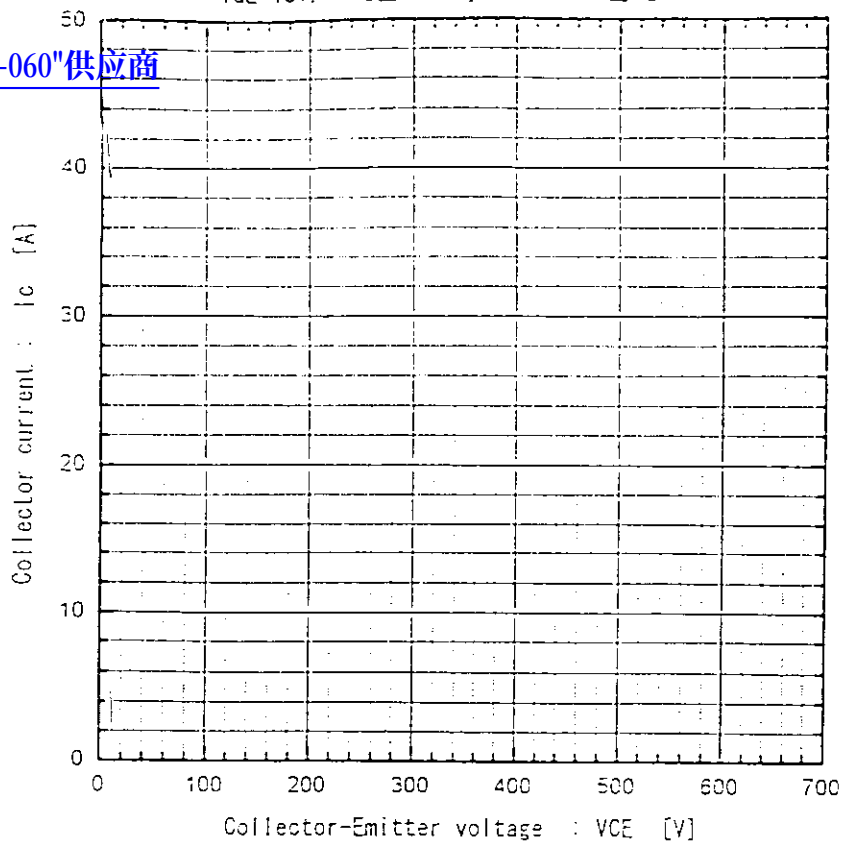
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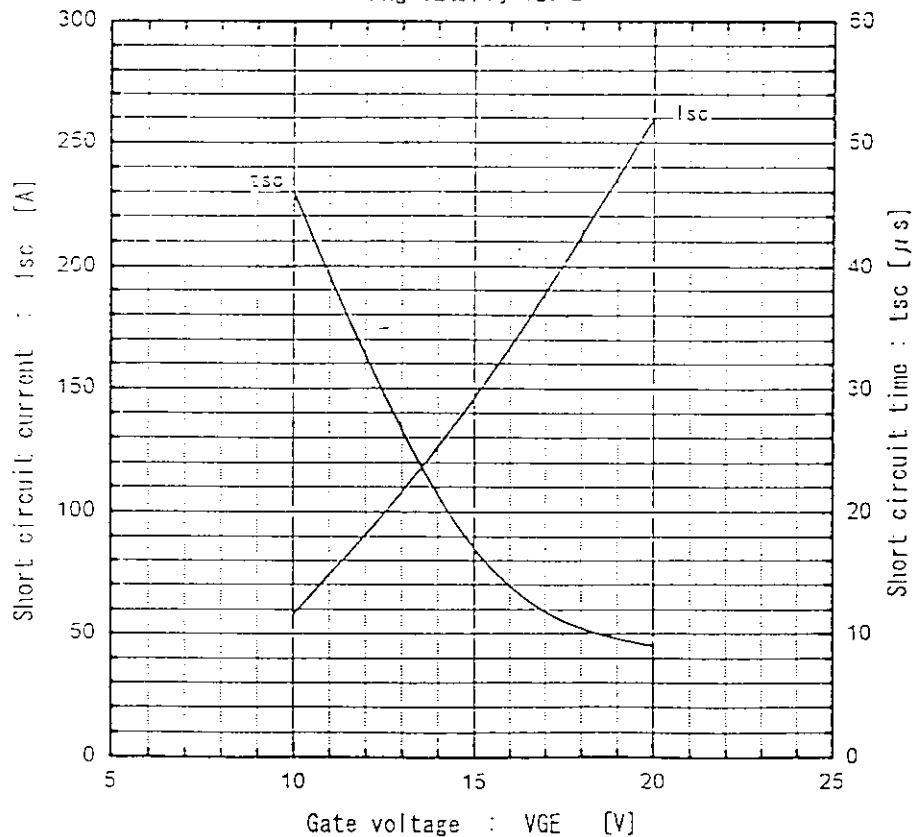
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Reverse Biased Safe Operating Area
 $-V_{GE} = -15V$, $-V_{GE} \leq 15V$, $T_j \leq 125^\circ C$, $R_g \geq 12\Omega$



Typical short circuit capability
 $V_{CC} = 400V$, $R_g = 12\Omega$, $T_j = 125^\circ C$



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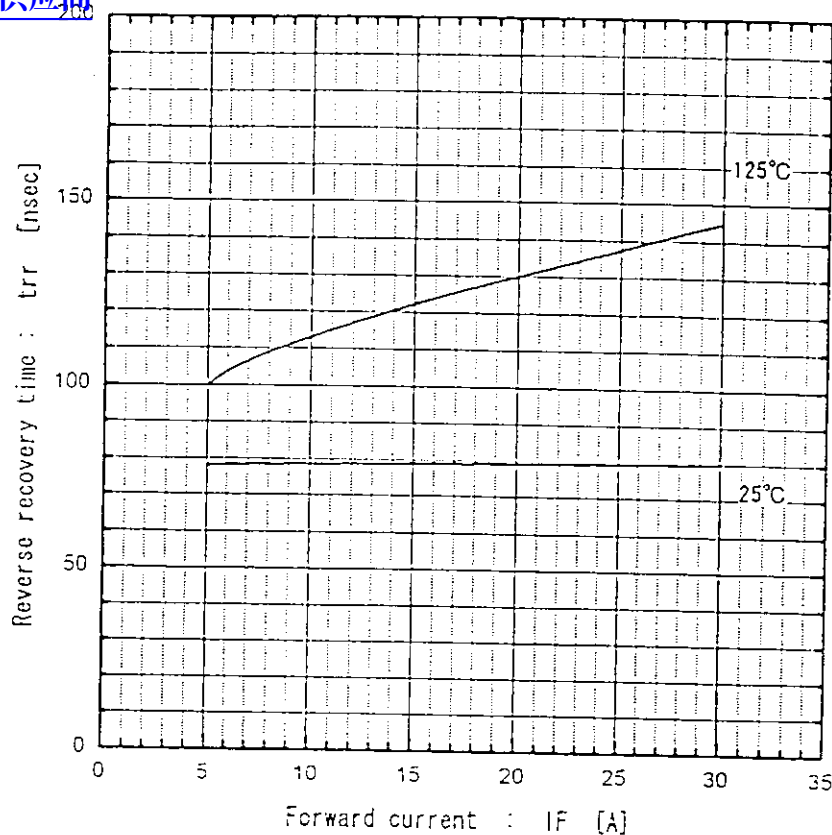
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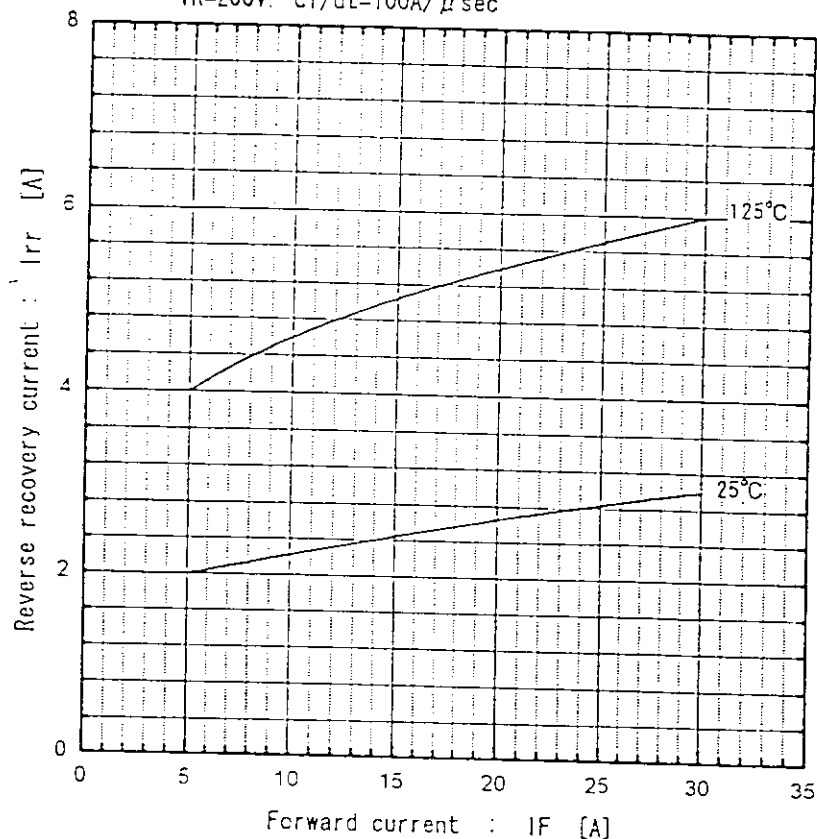
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Reverse recovery time vs. Forward current
VR=200V, $-di/dt=100A/\mu sec$

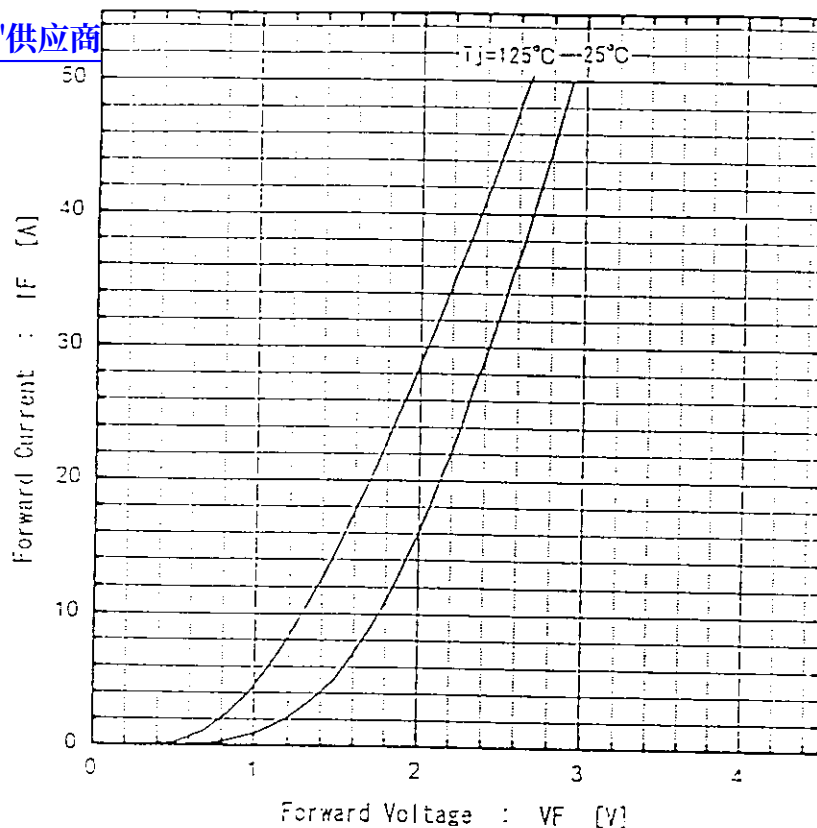


Reverse recovery current vs. Forward current
VR=200V, $-di/dt=100A/\mu sec$

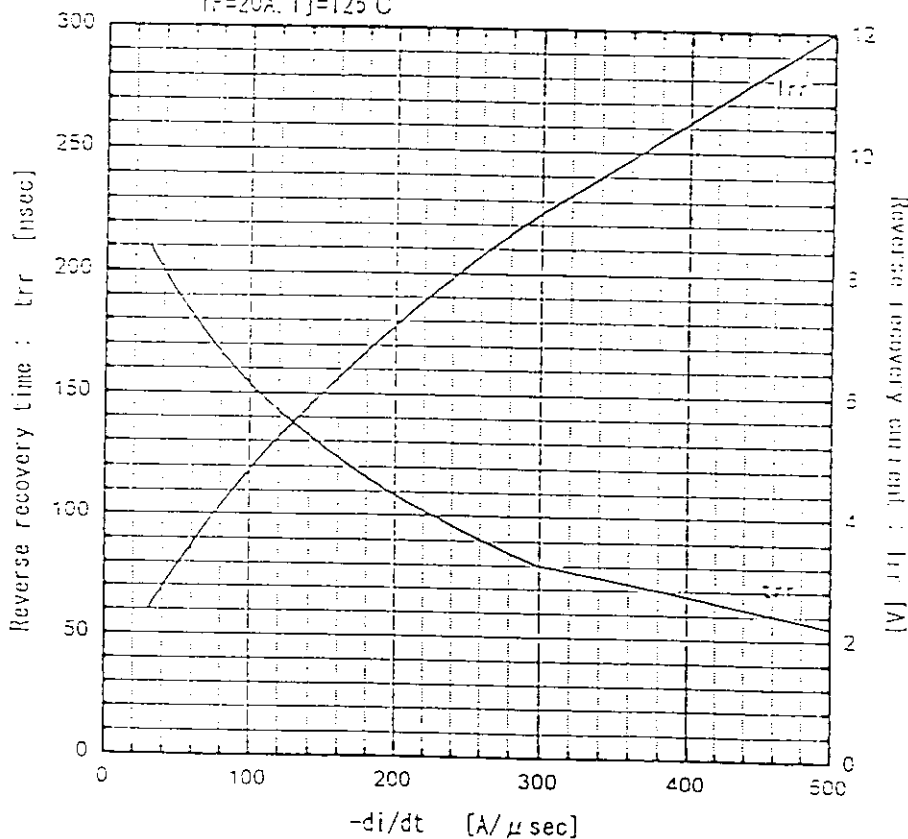


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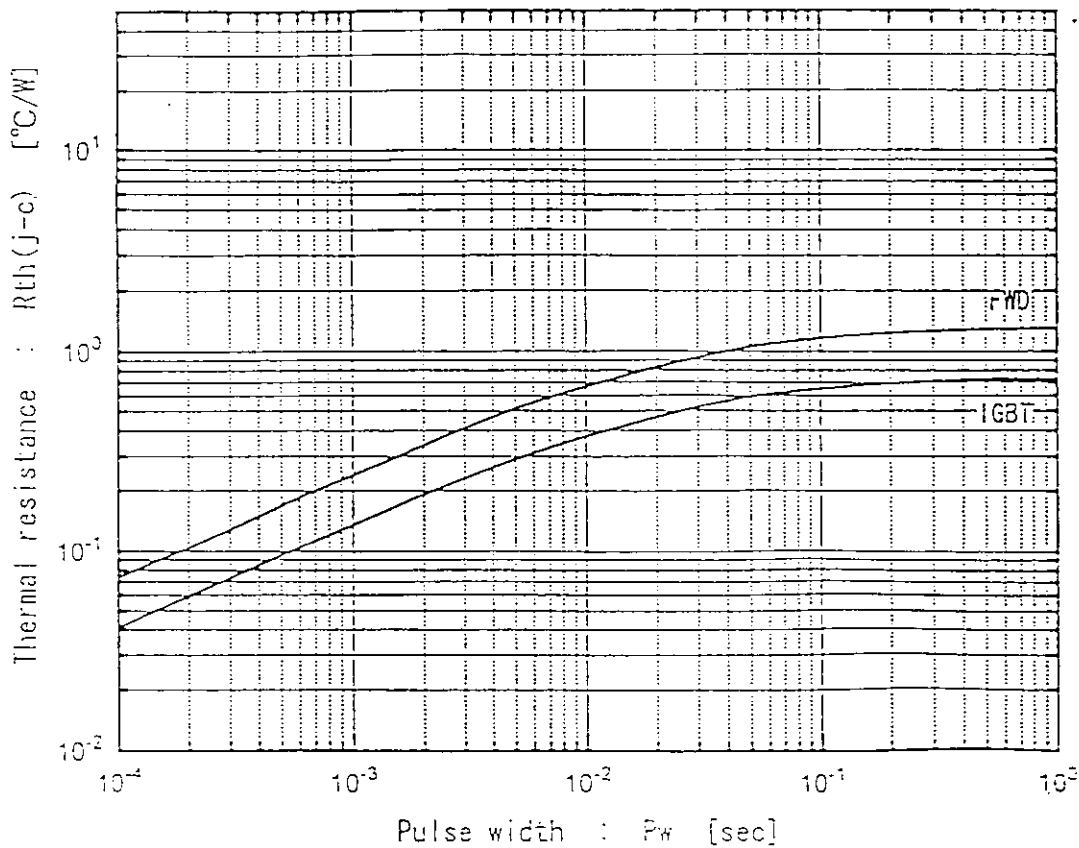
Forward voltage vs. Forward current



Reverse recovery characteristics vs. $-di/dt$
 $I_F = 20\text{A}$, $T_j = 125^\circ\text{C}$



Transient thermal resistance



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